## Electronic Supplementary Information

Anodizing with voltage versus optical path length modulation: a new tool for the preparation of photonic structures

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**Figure S2.** SEM images of cross-section of the sample S1250: upper part of AAO structure (a) and lower part of AAO structure (b). The scale bars are 500 nm. Distances from the top edges of (a) and (b) images to the top surface of the AAO film are 4 and 41  $\mu$ m, respectively. Red dashed and dotted lines represent edges between layers with lower and higher pore density.



**Figure S3.** Transmittance spectra of prepared anodic alumina photonic crystals: S250 (cyan), S400 (blue), S700 (red), S1000 (black), S1250 (violet), and S1400 (green). The spectra were recorded at an incident angle of 0°.



**Figure S4.** Transmittance spectra of prepared anodic alumina photonic crystals in narrow wavelength range around the first photonic band gap position: S250 (cyan), S400 (blue), S700 (red), S1000 (black), S1250 (violet), and S1400 (green). The spectra were recorded at an incident angle of 0°.